**Product data sheet** 

# 1. General description

EEPP<sup>™</sup>- Efficiency Enhanced Pt Planar rectifier in a 2-lead TO220 plastic package.

### 2. Features and benefits

- · Fast switching
- Reduces switching losses with improved lower reverse recovery charge
- · Soft recovery characteristics
- · Low thermal resistance
- · Low leakage current
- Planar termination structure
- High operating temperature capability (T<sub>j (max)</sub> = 175°C)
- Higher I<sub>FSM</sub> capability

# 3. Applications

- Switched-Mode Power Supplies
- Power factor correction diode
- Uninterrupted Power Supply

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions Values			Unit		
Absolute maximum rating							
$V_{RRM}$	repetitive peak reverse voltage		1200			V	
I <sub>F(AV)</sub>	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 120$ °C; Fig. 1; Fig. 2; Fig. 3	; 15			А	
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 120 °C; square-wave pulse	30			А	
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; <u>Fig. 4</u>	180			А	
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	200		Α		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.5	3.2	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	2.0	-	V
Dynamic	characteristics						
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	45	-	ns
Avalanche energy							
E <sub>AS</sub>	non-repetitive avalanche energy	$I_R = 4 \text{ A}; L = 5 \text{ mH}; T_{j(init)} = 25 \text{ °C}$		40	-	-	mJ

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode		K — A 001aaa020
mb	mb	mounting base; connected to cathode	1 2 TO-220AC (SOD59)	001aaa020

# 6. Ordering information

## **Table 3. Ordering information**

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYC15-1200P	TO220-2L	BYC15-1200PQ	Tube	50	SOD59	27-Nov-2012

# 7. Marking

### **Table 4. Marking codes**

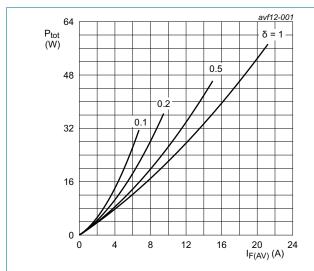
Type number	Marking codes
BYC15-1200P	BYC15 1200P

# 8. Limiting values

#### Table 5. Limiting values

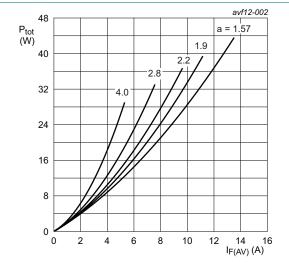
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		1200	V
$V_{\text{RWM}}$	crest working reverse voltage		1200	V
$V_R$	reverse voltage	DC	1200	V
I <sub>F(AV)</sub>	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 120$ °C; Fig. 1; Fig. 2; Fig. 3	15	А
I <sub>FRM</sub>	repetitive peak forward current	$δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 120 °C$ ; square-wave pulse	30	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	180	Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	200	А
T <sub>stg</sub>	storage temperature		-65 to 175	°C
T <sub>j</sub>	junction temperature		175	°C



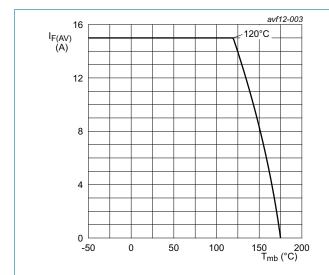
 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$  $V_o = 1.775 \text{ V}; \text{ R}_s = 0.0436 \Omega$ 

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 1.775 V;  $R_s$  = 0.0436  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values





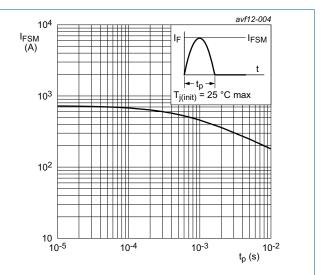


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	1.2	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

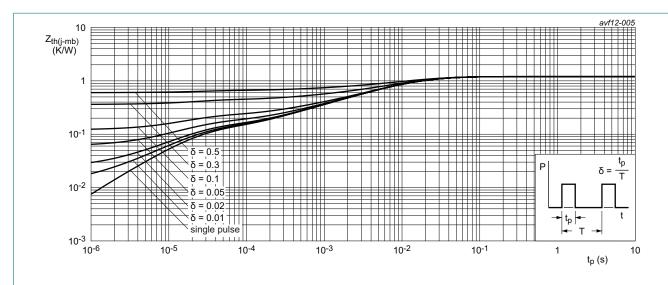
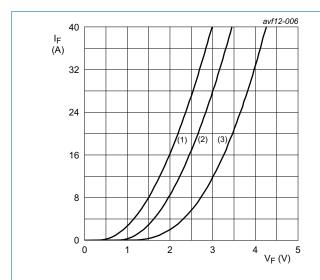


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

# 10. Characteristics

### **Table 7. Characteristics**

Symbol	l Parameter	Conditions	Min	Тур	Max	Unit
Static cl	haracteristics					
$V_{F}$	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2.5	3.2	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	2.0	-	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 1200 V; T <sub>j</sub> = 25 °C	-	-	100	μA
		V <sub>R</sub> = 1200 V; T <sub>j</sub> = 150 °C	-	-	500	μΑ
Dynami	c characteristics					
$Q_r$	recovered charge	$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	394	-	nC
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	1003	-	nC
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	1143	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	45	-	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	61	-	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	120	-	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	128	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	12.6	-	А
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	16.7	-	А
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 150 \text{ °C}; Fig. 7$	-	17.8	-	А
Avaland	che energy		,			
E <sub>AS</sub>	non-repetitive avalanche energy	$I_R = 4 \text{ A}; L = 5 \text{ mH}; T_{j(init)} = 25 \text{ °C}$	40	-	-	mJ





(1) T<sub>i</sub> = 150 °C; typical values

(2)  $T_i = 150$  °C; maximum values

(3)  $T_i = 25$  °C; maximum values

Fig. 6. Forward current as a function of forward voltage

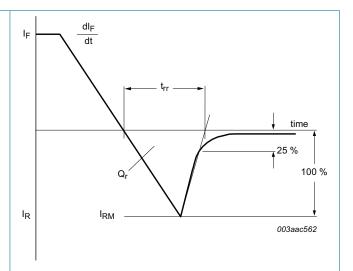
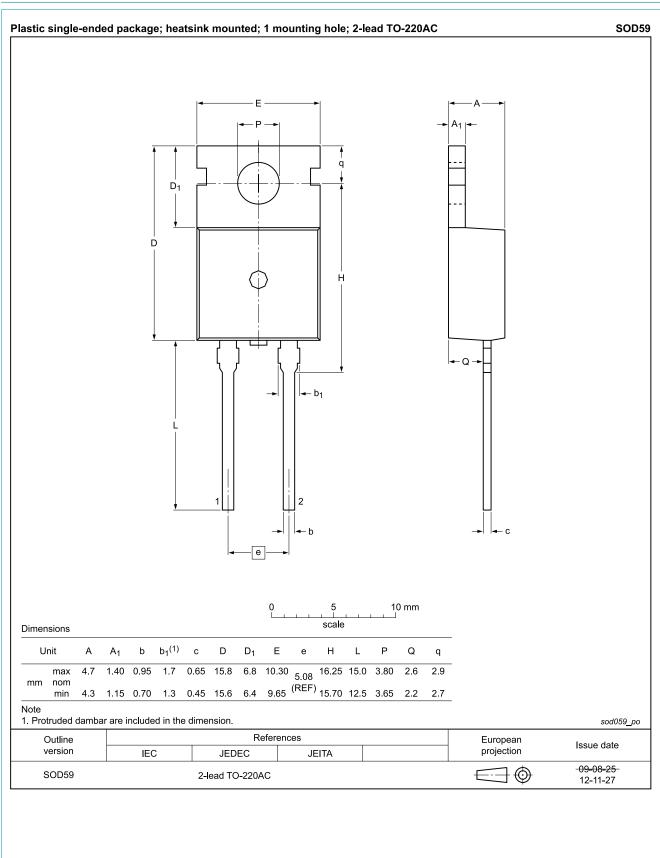


Fig. 7. Reverse recovery definitions; ramp recovery

# 11. Package outline



## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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